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REV SHEET REV	r			В			В		В		В				B 35			C 38								
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REV SHEET REV SHEET	TATUS	С	В 23	B 24	В	B 26	B 27	B 28	B 29	B 30	B 31	32	33	34 C	35	36 C	37	38							B 20	t
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DESC FORM 193-1 SEP 87

DRAWING

THIS DRAWING IS AVAILABLE

FOR USE BY ALL DEPARTMENTS

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DEPARTMENT OF DEFENSE

• U.S. GOVERNMENT PRINTING OFFICE: 1987 — 748-129/60912 5962-E1498-2

OF

85010

MICROCIRCUITS, 16-BIT N-CHANNEL MICRO-

PROCESSOR, MONOLITHIC SILICON

CAGE CODE

14933

1

SIZE

Α

SHEET

DRAWING APPROVAL DATE

18 OCTOBER 1985

С

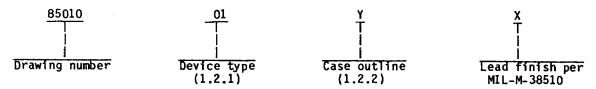
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REVISION LEVEL

	ΩP	

 $1.1\,$ Scope. This drawing describes device requirements for class B microcircuits in accordance with $1.2.1\,$ of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".

1.2 Part number. The complete part number shall be as shown in the following example:



1.2.1 Device types. The device types shall identify the circuit function as follows:

Device type	Generic number	Frequency	Circuit
01	M80186	8 MHz	16-bit N-channel microprocessor
02	M80186	6 MHz	16-bit N-channel microprocessor

1.2.2 Case outlines. The case outlines shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter

Y Z

Case outline

68-terminal ceramic quad package (see figure 1) P-AC (1.160" X 1.160"), pin grid array package

1.3 Absolute maximum ratings.

1.4 Recommended operating conditions.

Supply voltage range (V _{CC}):	4.75 V V V 5.05 V V
Device type 01	4.75 V dc to 5.25 V dc
Device type 02	4.75 V dc to 5.25 V dc
Frequency of operation:	
Device type 01	8 MHz
Device type 02	6 MHz
Case operating temperature range (T_C)	-55°C to +125°C

STANDARDIZED MILITARY DRAWING

DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444

SIZE A	Α	35010		
		REVISION LEVEL	SHEET	2

2. APPLICABLE DOCUMENTS

2.1 Government specification, standard, and bulletin. Unless otherwise specified, the following specification, standard, and bulletin of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510 - Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

BULLETIN

MILITARY

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

(Copies of the specification, standard, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
 - 3.2.1 Terminal connections. The terminal connections shall be as specified on figure 2.
 - 3.2.2 Functional block diagram. The functional block diagram shall be as specified on figure 3.
 - 3.2.3 Case outlines. The case outlines shall be in accordance with 1.2.2 herein.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and apply over the full recommended case operating temperature range.
- 3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.
- 3.5 Marking. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in MIL-BUL-103 (see 6.7 herein).

STANDARDIZED MILITARY DRAWING	SIZE A			85010	
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISIO	N LEVEL C	SHEET	3

	TABLE I.	Electrical performance char	racteris	tics.			
Test	Symbol	-55°C < T _C < +125°C V _{CC} = 5.0 V ±5%	 Device type 	Group A isubgroups		mits	Unit
	1	lunless otherwise specified	 	 	Min	Max	<u> </u>
Low-level input voltage	VIL		01, 02	1,2,3	-0.5	+0.8	V
High-level input voltage (All except X1 and (RES))	V _{IH1}		01, 02	1,2,3	2.0	V _{CC} +0.5	i V
High-level input voltage at (RES)	V _{IH2}		01, 02	1,2,3	3.0	V _{CC} +0.5	V
Low-level output voltage	VOL	I_{OL} = 2.5 mA for \overline{SO} - \overline{SZ} I_{OL} = 2.0 mA for all other outputs	01, 02	1,2,3		0.45	 V
High-level output voltage	VOH	I _{OH} = -400 μA	01, 02	1,2,3	2.4		V
Power supply current	1 CC	VCC = 5.25 V	01, 02	1,2,3		600	mA
Input leakage current	IIL	O A < AIN < ACC	01, 02	1,2,3		±10	μA
Output leakage current	IOL	10.45 V < Y _{OUT} < Y _{CC}	01, 02	1,2,3		 ±10	μA
Low-level clock output voltage	Y _{CLO}	I ₀ = 4.0 mA	01, 02	1,2,3		0.6	V
High-level clock output voltage	V _{СНО}	$I_0 = -200 \mu A$	01, 02	1,2,3	4.0	İ 	i v
Low-level clock input voltage	Y _{CL1}		01, 02	1,2,3	-0.5	+0.6	V
High-level clock input voltage	V _{CH1}		01, 02	1,2,3	3.9	 V _{CC} +1.0	V
Functional tests		 See 4.3.1d	 01, 02	7,8	ı		
	CIN		01, 02		 	10	l pF
I/O capacitance	C 10	See 4.3.1c	01, 02			20	l pF

See footnotes at end of table.

STANDARDIZED MILITARY DRAWING	SIZE A			85010	
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	,	SHEET	4

TABLE I.	Electric	al p	erformance	e chara	acterist	ics - C	ontinued.			
Test	Symbol	 -5	Conditio 55°C < Tc V _{CC} = 5.0	< +125	°C		Group A subgroups	Limit	:s	Unit
	i I	unle	ess otherw	ise sp	ecified			Min	Max	
Data in setup (A/D)	t _{DVCL}		= 20 to 2 tputs	00 pF,	all	01,02	9,10,11	20		ns
Data in hold (A/D)	t _{CLDX}					01,02	 9,10,11 	10	 	ns I
Asynchronous ready (AREADY) active setup time	t _{ARYHCH}					01,02	9,10,11	20		ns
AREADY inactive setup time	t _{ARYLCL}]] [!	01,02	9,10,11	38		ns
AREADY hold time	[‡] CHARYX				1	01,02	9,10,11	15		ns
Synchronous ready (SREADY) transition setup time	^t srycl		•			01,02	9,10,11	35		ns
SREADY transition hold time	t _{CLSRY}					01,02	9,10,11	15		ns
Hold setup <u>2</u> /	thycl	 -				01,02	 9,10,11 	25]]	l ns
INTR, NMI, TEST, TIMERIN setup <u>2</u> /	tinvch	 				 01,02 	 9,10,11 	25		ns
DRQO, DRQ1, setup	tINVCL					01,02	9,10,11	25		ns
Address valid delay	tCLAV	 				01	9,10,11	5	59	l ns
	-					02	9,10,11	5	63	ns
Address hold	t _{CLAX}	j I			•	01	9,10,11	5	<u> </u>	ns
		<u> </u>				02	9,10,11	5	<u> </u>	ns
Address float delay	tCLAZ					01	9,10,11	tCLAX	35	ns
	 					02	9,10,11	tCLAX	44	ns
Address valid to clock high	tavch	 		<u></u>		01,02	9,10,11	10	 	l ns
See footnotes at end of tab	le.									
STANDARDIZEI MILITARY DRAW			SIZE					85010		
DEFENSE ELECTRONICS SUPP DAYTON, OHIO 4544	PLY CENTER				REVISIO	N LEVEL C		SHEET	5	

TABLE	I. Elec	trical performance charact	eristics	- Continu	ed.		
Test	Symbol	Condition 1/ -55°C < T _C < +125°C	type	Group A subgroups	Limi	ts	Unfi
		V _{CC} = 5.0 V ±5% unless otherwise specifie	1	! 	Min	Max	<u> </u>
Command lines float	tchcz	C _L = 20 to 200 pF, all	01	9,10,11		45	ns
delay		oūtputs 	02	9,10,11		56	ns
Command lines valid delay (after float)	tCHCV		01	9,10,11		55	ns
	<u> </u>	' 	02	9,10,11		76	ns
ALE width	tLHLL		01,02	9,10,11	t _{CL} çL		ns
ALE active delay	tCHLH	1	01	9,10,11	 	35	l l ns
	<u> </u>	1 	02	9,10,11	 	44	ns
ALE inactive delay	tCHLL		01	9,10,11	 	35	ns
	<u> </u>		02	9,10,11		44	<u> </u> ns
Address hold to ALE inactive	tLLAX		01	9,10,11	tcHCL -25		ns
] 	1 1 1	02	9,10,11	t _{CHCL}		l ns
Data valid delay	tCLDV		01	9,10,11	5	44	ns
	ļ	_	02	9,10,11	5	55	-
Data hold time	tCLDOX		01,02	9,10,11	5		ns
Data hold after WR	tWHDX	-1 	01	9,10,11	t _{CLCL} -40		ns
			02	9,10,11	^t cւ <u>գ</u> ե		ns
Control active delay 1	tcvcTv		01	9,10,11	5	70	ns
	<u> </u>	_	02	9,10,11	5	87	ns
Control active delay 2	tCHCTV		01	9,10,11	5	73	i ns
	<u> </u>		02	9,10,11	5	76	i ns
DEN inactive delay (non-write cycle)	tCVDEX		01	9,10,11	10	70	ns
See footnotes at end of	table.	1	<u> 02</u>	9,10,11	1 10	l 87	l n
STANDARD MILITARY DR		SIZE A			850	10	
DEFENSE ELECTRONICS DAYTON, OHIO	SUPPLY CE		EVISION L	EVEL.	SHI	ET 6	

TABL	E I. Elec	ctrical pe	erformance	charact	eristics	- Continu	ed.		
Test	Symbol	Con	dition <u>1/</u>	.5°C	Device type	Group A subgroups	Limi	ts	Unit
		unless o	$< T_C < +\overline{1}2$ = 5.0 V ±5 therwise s	pecified	1		Min	Max	
Address float to RD active	tazrl	CL = 20 loutputs	to 200 pF,	all	01,02	9,10,11	0	 	ns
RD active delay	t _{CLRL}	1			01	9,10,11	10	70	ns
	<u> </u>	<u> </u>			02	9,10,11	10	87	ns
RD inactive delay	tclrh	 			01	9,10,11	10	55	ns
		-			02	9,10,11	10	76	ns
RD inactive to address active	trhay				01	9,10,11	[‡] Շ <u>Ի</u> գե		ns
	1 	 -	,		02	9,10,11	tclgl] 	ns
HLDA valid delay	tCLHAV				01,02	9,10,11	! 5 	67	ns
ŔD width	t _{RLRH}	- 			01,02	9,10,11	2t _{CLCL} -50		ns
WR width	twlwh] 			01,02	9,10,11		 	l ns
Address valid to ALE low	t _{AVAL}	1 			01	9,10,11	t _{CLCH}		ns
	! !				02	9,10,11	 ^Է Շ <u>Ի</u> գե		ns
Status active delay	tchsv	- 			01	9,10,11	10	55	ns
	<u> </u>	_[02	9,10,11	10	76	ns
Status inactive delay	^t CLSH				01	9,10,11	10	65	ns
	<u> </u>	<u> </u>			02	9,10,11	10	76	ns
Timer output delay	tCLTMV	C _L = 100) pF maxim	um	01	9,10,11	<u> </u>	60	ns
				· · · · · · · · · · · · · · · · · · ·	02	9,10,11		75	ns
Control inactive delay	tcvctx		to 200 pF	, all	01	9,10,11	5	55	ns
		outputs			02	9,10,11	5	76	ns
See footnotes at end of	table.								
STANDARD			SIZE A		· · · · · · · · · · · · · · · · · · ·		850	010	
MILITARY DE DEFENSE ELECTRONICS DAYTON, OHIO	S SUPPLY CE			R	EVISION L	.EVEL C	SHE		

Test	Symbol	1 -55°C < Tr < +125°C	l type	 Group A subgroups	Limit	Unit		
	<u> </u>	V _{CC} = 5.0 V ±5% lunless otherwise specified	 		Min	Max) 	
Reset delay	tCLRO	C _L = 20 to 200 pF, all outputs	01	9,10,11		60	ns	
· · · · · · · · · · · · · · · · · · ·	<u> </u>	1	02	9,10,11	<u>i</u>	75	ns	
Queue status delay	tcHQSV		01	9,10,11		35	ns	
	<u> </u>		02	9,10,11		44	ns	
Chip-select active	t _{CLCSV}	1	01	9,10,11	5	66	ns	
delay	<u> </u>		02	9,10,11	5	80	ns	
Chip-select hold from command inactive	tcxcsx		01,02	9,10,11	35		ns	
Chip-select inactive delay	tCHCSX		01,02	9,10,11	5	47	ns	
CLKIN period	tCKIN		01	9,10,11	62.5	250	ns	
	1		02	9,10,11	83	250	ns	
CLKIN fall time	tCKHL	3.5 V to 1.0 V <u>3</u> /	01,02	9,10,11		10	ns ns	
CLKIN rise time	t _{CKLH}	1.0 V to 3.5 V <u>3</u> /	01,02	9,10,11		10	l ns	
CLKIN low time	tclck	1.5 V <u>3</u> /	01	9,10,11	25		ns	
	ļ		02	9,10,11	33		ns	
CLKIN high time	‡CHCK	1.5 V <u>3</u> /	01	9,10,11	25		ns	
	1		02	9,10,11	33	<u> </u>	ns	
CLKIN to CLKOUT skew	‡CICO	C _L = 20 to 200 pF, all	01	9,10,11		50	ns	
	<u> </u>		02	9,10,11		62.5	ns	
CLKOUT period	tCLCL		01	9,10,11	125	500	ns	
	<u> </u>		02	9,10,11	167	500	ns	
CLKOUT low time	tCLCH	1.5 V <u>3</u> /	01,02	9,10,11	1/2 t _{CLCL} -7.5		ns	
See footnotes at end of	table.	· · · · · · · · · · · · · · · · · · ·			-7.31	*:_		
STANDARD	IZED AWING	SIZE A			85010			

DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444

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REVISION LEVEL.

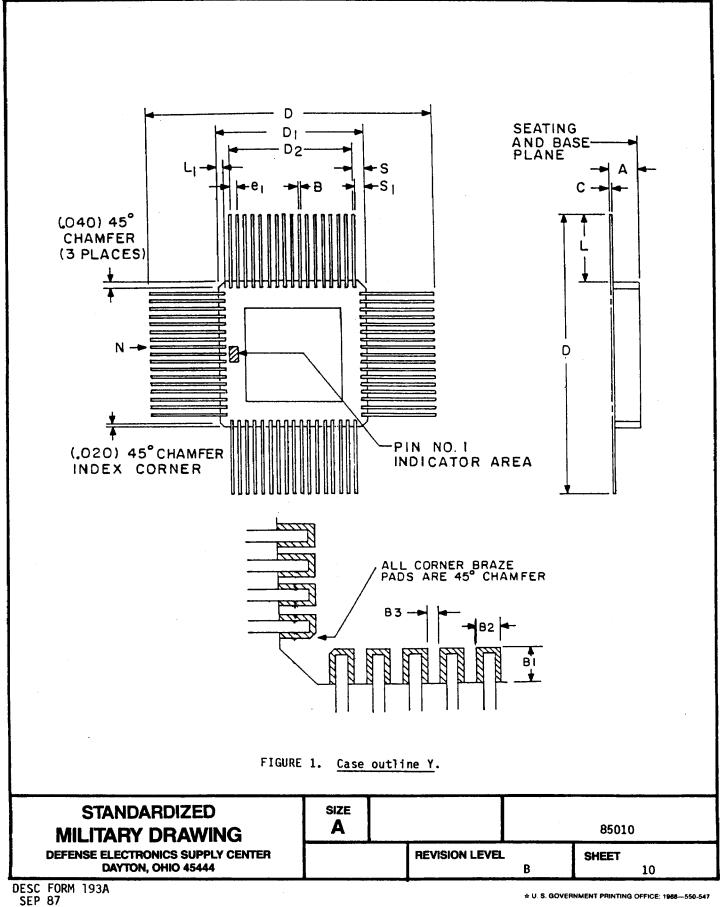
Test	Symbol	-55°C < Tc < +T25°C		 Group A subgroups	Limit	s	 Unit
		V _{CC} = 5.0 V ±5% unless otherwise specified	<u> </u>	! !	Min	Max	1
CLKOUT high time	tCHCL	1.5 V <u>3</u> /	 01,02 	9,10,11	1/2 t _{CLCL} -7.5		ns
CLKOUT rise time	tCH1CH2	1.0 V to 3.5 V 3/	01,02	9,10,11		15	ns
CLKOUT fall time	tCL2CL1	3.5 V to 1.0 V 3/	01,02	9,10,11	 	15	ns

 $[\]underline{1}$ / All ac parameters tested as per circuit on figure 4.

STANDARDIZED MILITARY DRAWING	SIZE A			85010	
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LI	E VEL C	SHEET	9

 $[\]underline{2}$ / Setup requirements only to guarantee recognition at next CLK.

 $[\]underline{3}$ / Voltage indicated refer to voltage measurements on waveforms in figure 4.



Dimensions									
Ltr	Inche	es .	Millin	neters					
	Min	Max	Min	Max					
Α	.080	.106	2.03	2.69					
В	.016	.020	0.41	0.51					
B ₁	.040	.060	1.02	1.52					
B ₂	.030	.040	0.76	1.02					
83	.005	.020	0.13	0.51					
С	.008	.012	0.20	0.30					
D	1.640	1.870	41.66	47.50					
D ₁	.935	.970	23.75	24.64					
D ₂	.800	BSC	20.32 BSC						
e ₁	.050	BSC	1.27	BSC					
L	.375	.450	9.53	11.43					
L ₁	.040	.060	1.02	1.52					
N	68 F	PINS	68 F	INS					
S	.Q66	.087	1.68	2.21					
s ₁	.050		1.27						

FIGURE 1. <u>Case outline Y</u> - Continued.

STANDARDIZED MILITARY DRAWING	SIZE A				85010	
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		· · · · · · · · · · · · · · · · · · ·	REVISION LEVEL	С	SHEET	

Case outline Y

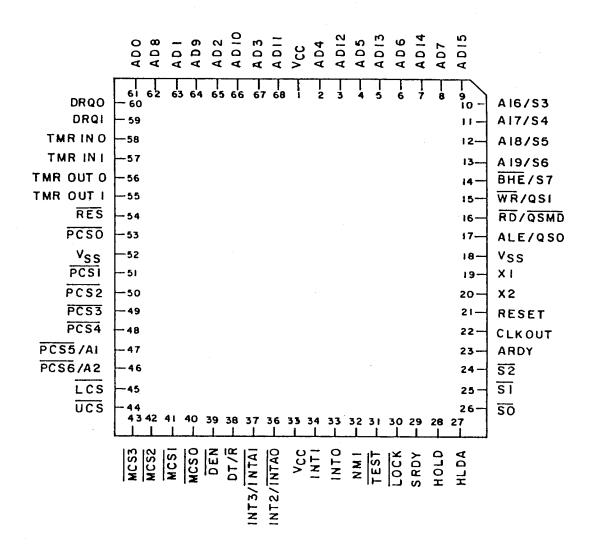


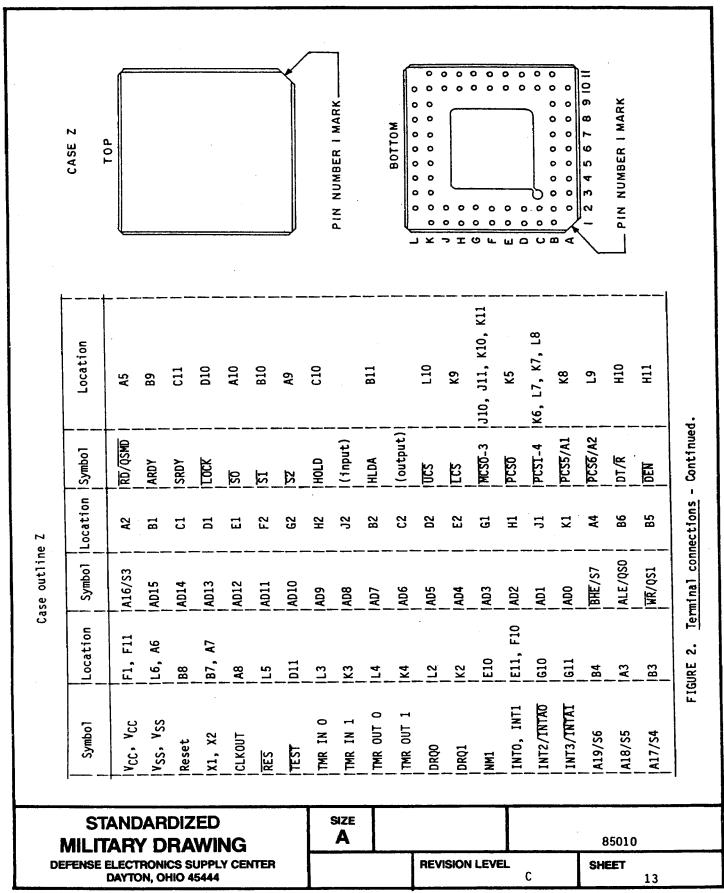
FIGURE 2. Terminal connections.

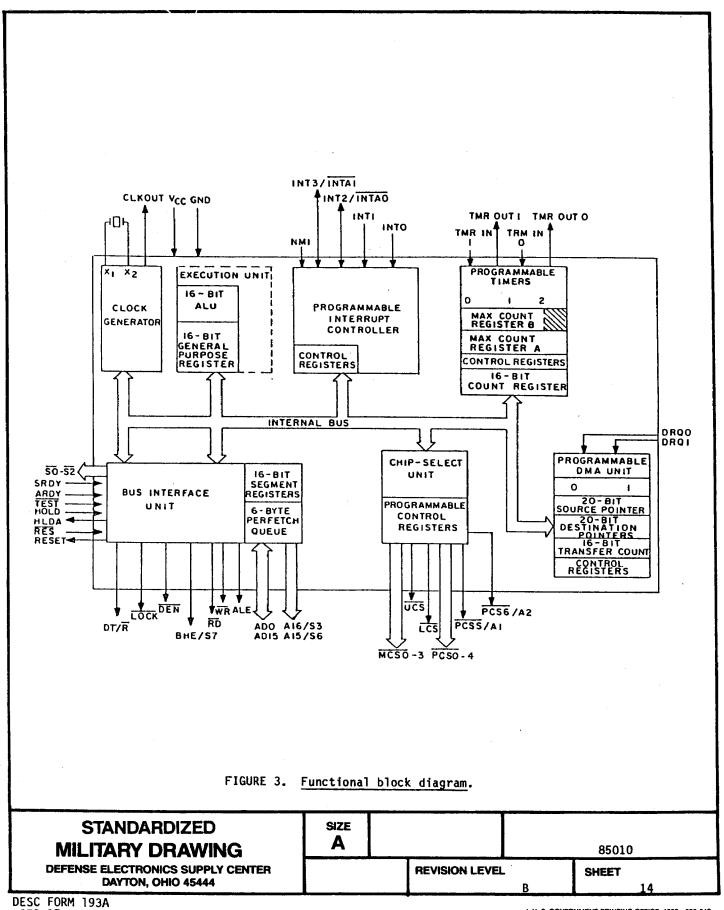
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MILITARY DRAWING
DEFENSE ELECTRONICS SUPPLY CENTER
DAYTON, OHIO 45444

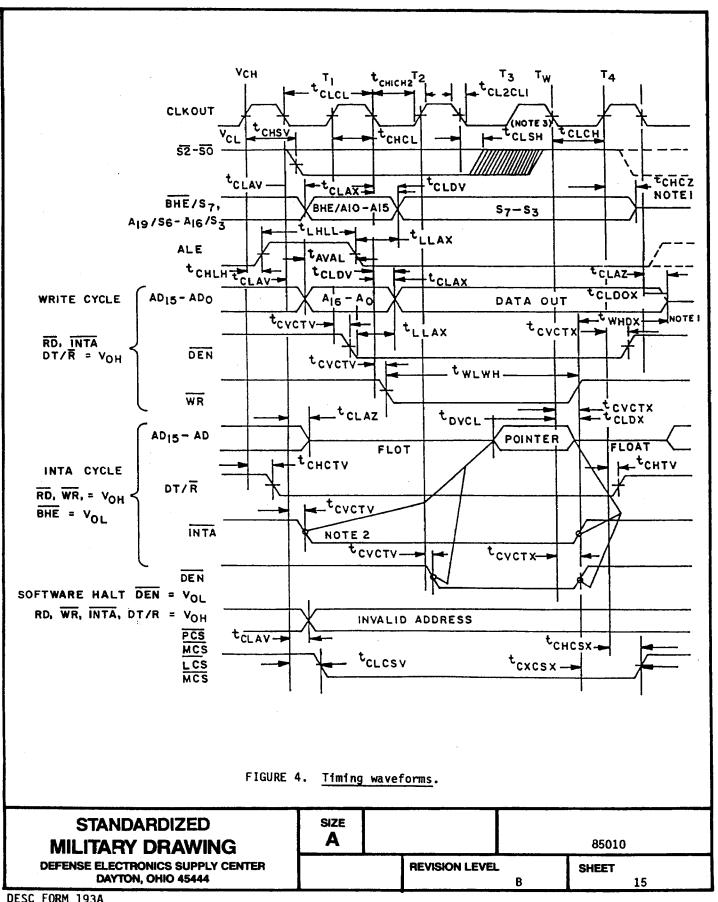
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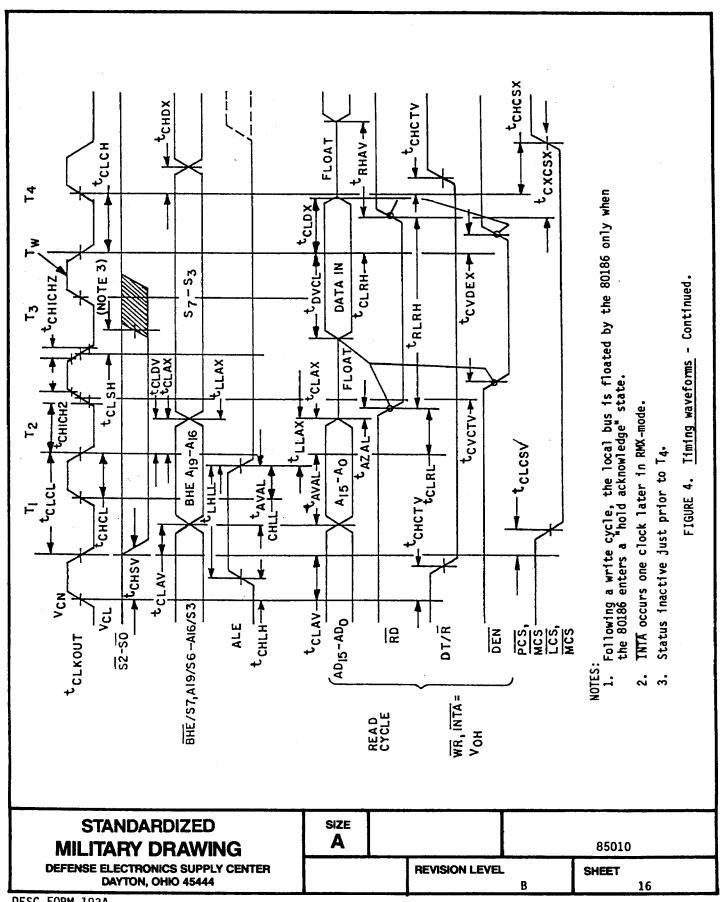
85010

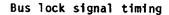
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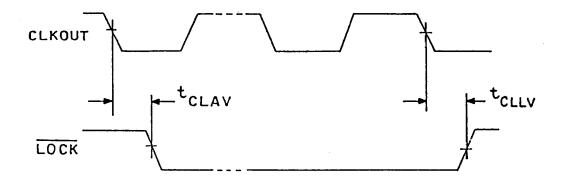












Asynchronous signal recognition

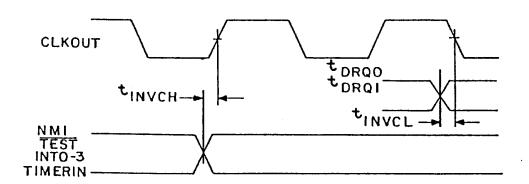
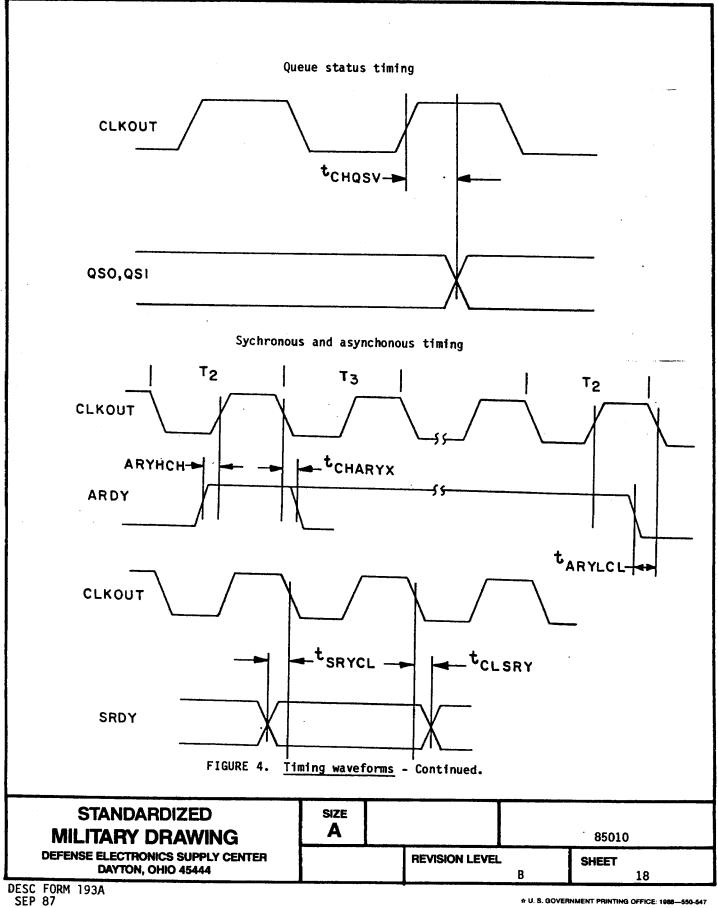
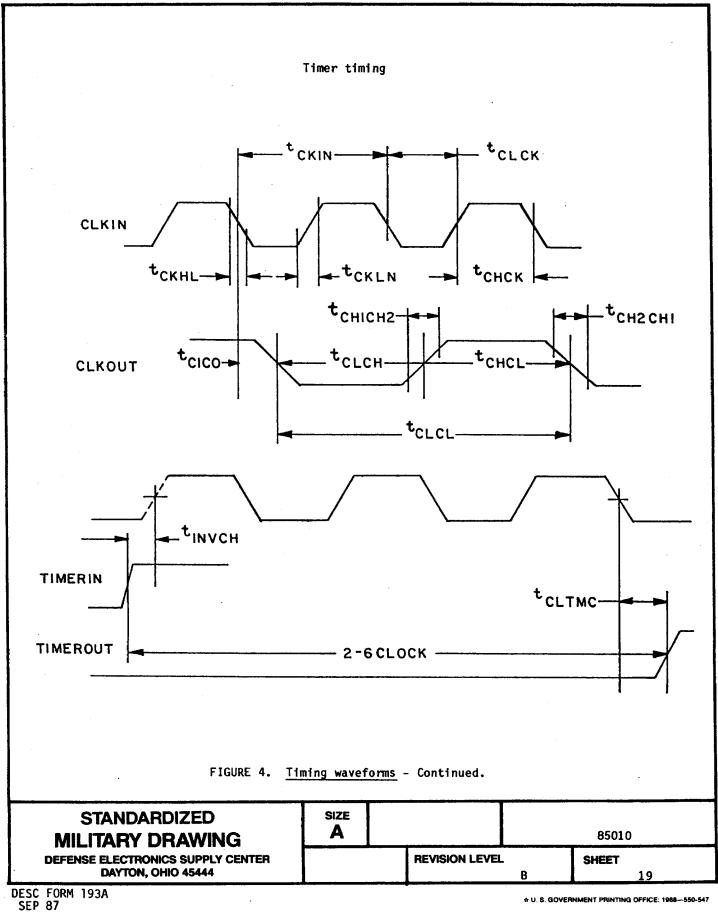
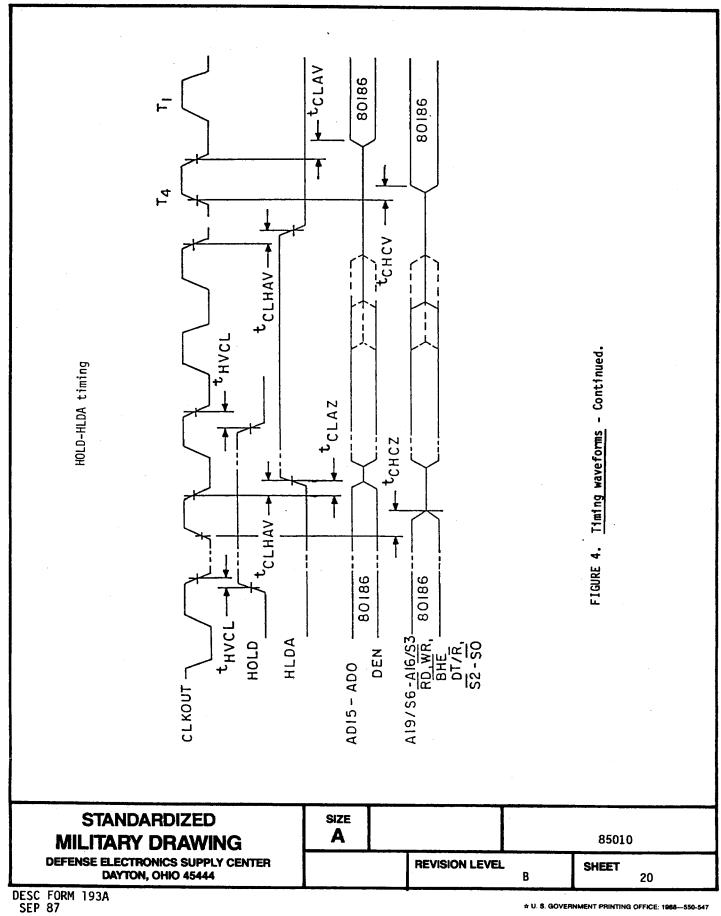


FIGURE 4. Timing waveforms - Continued.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444 SIZE A 85010 REVISION LEVEL B 17







- 3.6 Certificate of compliance. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7 herein). The certificate of compliance submitted to DESC-ECC prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.7 Certificate of conformance. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.9 Verification and review. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
 - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.7 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
 - 4.3.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
 - c. Subgroup 4 ($C_{\rm IN}$ and $C_{\rm IO}$ measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance. A minimum sample size of five devices with zero rejects shall be required.
 - d. Subgroups 7 and 8, functional testing shall include verification of instruction set (see table III).

						
STANDARDIZED MILITARY DRAWING	SIZE A			85	010	
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	·	RE	E VISION LEVE L	-	SHEET	21

TABLE II. Electrical test requirements.

 MIL-STD-883 test requirements 	Subgroups (per method 5005, table I)
 Initial electrical parameters (method 5004) 	
 Final electrical test parameters (method 5004) 	1*, 2, 3, 7, 8, 9, 10, 11
Group A test requirements (method 5005)	1 1, 2, 3, 4, 7, 8, 9, 10, 11
Groups C and D end-point electrical parameters (method 5005)	 2, 8(+125°C), 10

^{*} PDA applies to subgroup 1.

4.3.2 Groups C and D inspections.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Steady-state life test conditions, method 1005 of MIL-STD-883.
 - (1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.7 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) Test duration: 1,000 hours, except as permitted method 1005 of MIL-STD-883.

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	TABLE III.	Instruc	tion set	summa	iry.			
Function	Format						 Clock cycles	Comments
DATA TRANSFER								
MOV = Move: Register to register/memory	1 0 0 0 1 0 0	bom w C	reg r	·/m			2/12	
Register/memory to register	100010	l w mod	reg 1	·/m			2/9	
Immediate to register/memory	1 1 0 0 0 1	1 w mod	000	'/m d	data data	if w = 1	12-13	8/16-bit
Immediate to register	1 0 1 1 w	reg	data	da	ata if w =	1	3-4	8/16-bit
Memory to accumulator	1 0 1 0 0 0	0 w	addr-lo	ı a	addr-high		9	į
Accumulator to memory	1 0 1 0 0 0	1 w	addr-10	v a	addr-high		8	
Register/memory to segment register	1 0 0 0 1 1	1 0 mod	0 reg	r/m			2/9	
Segment register to register, memory	100011	0 0 mod	l O reg	r/m			2/11	
PUSH = Push: Memory	1 1 1 1 1 1	1 1 mod	1110	r/m			16	<u> </u>
Register	0 1 0 1 0 re	g					10	
Segment register	0 0 0 reg 1	1 0					9	
Immediate	0 1 1 0 1 0	s 0	data		data if s =	0	10	
PUSHA = Push All	0 1 1 0 0 0	0 0					36	
POP = Pop: Memory	1 0 0 0 1 1	1 1 mod	1000	r/m			20	
Register	0 1 0 1 1	reg					10	
Segment register	0 0 0 reg 1	1 1	(reg ≠ 0	1)			8	
POPA = Pop All	0 1 1 0 0 0	0 1					51	
XCHG = Exchange: Register/memory with registe	r 1 0 0 0 0 1	1 w mo	d reg r	/m			4/17	
Register with accumulator	10010 r	eg					3	!
<pre>IN = Input from: Fixed port</pre>	1 1 1 0 0 1	0 w	port				10	
Variable port	1 1 1 0 1 1	0 w					8	
						<u></u>	<u> </u>	<u>i</u>
STANDARDIZED		SIZE						
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TABLE III. <u>Instruction set summary</u> - Continued.									
Function	Format					Clock cycles	 Comments		
OUT = Output to: Fixed port	1110011	w nont 1					j j		
Variable port	1 1 1 0 1 1 1					9 _	} !		
XLAT = Translate byte to AL	1 1 0 1 0 1 1					7			
LEA = Load EA to register	1000110		r/m	1		11			
LDS = Load pointer to DS	1 1 0 0 0 1 0		r/m	(mad / 11)		6			
LES = Load pointer to ES	1 1 0 0 0 1 0		r/m	(mod ≠ 11)		18 			
LAHF = Load AH with flags	1001111		17111	(mod ≠ 11)		18			
SAHF = Store AH into flags	1001111					2			
PUSHF = Push flags	1001111					3 			
POPF = Pop flags	1001110	===				9 ! _			
SEGMENT = Segment Override:	1001110					8 			
CS	0 0 1 0 1 1 1	0				2			
SS	0 0 1 1 0 1 1	0				2			
DS	0 0 1 1 1 1 1	0				2			
ES	0010011	0				2			
ARITHMETIC ADD = Add: Reg/memory with register to either	0000000	w mod reg	r/m			3/10			
Immediate to register/memory	100000s	w mod 0 0	r/m	data data if s	w=01	4/16			
Immediate to accumulator	0000010	w dat	3	data if w = 1	/ _[8/16-bit		
ADC = Add with carry: Reg/memory with register to either	0 0 0 1 0 0 d	w mod reg	r/m		 - - 	3/10			
Immediate to register/memory	1 0 0 0 0 0 s	w mod 0 1 () r/m	data data if s	w=01	4/16			
Immediate to accumulator	0 0 0 1 0 1 0	w da	a d	ata if w = 1		3/4	8/16-bit		
<pre>INC = Increment: Register/memory</pre>	111111	w mod 0 0 () r/m		 	3/15	,		
Register	0 1 0 0 0 re	g				3			
		·		-					
STANDARDIZED		SIZE			······································				
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TABL	E III. <u>Instr</u>	uction se	t summary	Contin	ued.			
Function	Format						Clock cycles 	Comments
SUB = Subtract: Reg/memory and register to either	0 0 1 0 1 0	d w mod	reg r/	m			 3/10 	
Immediate from register/memory	100000	s w mod	101r/	m data	data i	f s w=01	4/16	i 1
Immediate from accumulator	0 0 1 0 1 1	0 w	data	data ii	f w = 1		3/4	8/16-b1t
SBB = Subtract with borrow: Reg/memory and register to either	0 0 0 1 1 0	d w mod	reg r	m			3/10	
Immediate from register/memory	100000	sw mod	0 1 1 r	m data	data i	f s w=01	4/16	
Immediate from accumulator	0 0 0 1 1 1	0 w	data	data i	f w = 1		3/4	8/16-bit
DEC = Decrement: Register/memory	111111	1 w mod	001	·/m			j . 3/15	
Register	01001 r	eg					3	1
CMP = Compare: Register/memory with register	0 0 1 1 1 0	1 w mod	reg r/m	1			3/10	i !
Register with register/memory	0 0 1 1 1 0	0 w mod	reg r/r				3/10	1
Immediate with register/memory	100000	s w mod	111r	m data	data i	f s w=01	3/10	
Immediate with accumulator	0 0 1 1 1 1	0 w 0	data	data i	f w = 1		3/4	8/16-bit
NEG = Change sign	1 1 1 1 0 1	1 w mod	0 1 1	·/m			j 3	i
AAA = ASCII adjust for add	0 0 1 1 0 1	1 1					1 8	į
DAA = Decimal adjust for add	0 0 1 0 0 1	1 1					1 4	į
AAS = ASCII adjust for subtract	0 0 1 1 1 1	1 1					7 	İ :
DAS = Decimal adjust for substract	0 0 1 0 1 1	1 1					4	
MUL = Multiply (unsigned): Register-Byte Register-Word Memory-Byte Memory-Word	1 1 1 1 0 1	1 w mod		·/m			 26-28 35-37 32-34 41-43	
IMUL = Integer multiply (signed): Register-Byte Register-Word Memory-Byte Memory-Word	111101	1 w mod	1101	r/m			 25-28 34-37 31-34 40-43	1
STANDARDIZED	1	SIZE A				85010		
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Т	ABLE III. Ins	truction s	et sum	mary -	Conti	nued.				
Function	Format								Clock cycles	Comments
ARITHMETIC (Continued):					·			- i		<u> </u>
IMUL = Integer immediate multiply (signed)	0 1 1 0 1 0	s 1 mod	l reg	r/m	data	data	1f s =		22-25/! 29-32	
DIV = Divide (unsigned):	1 1 1 1 0 1	1 w mod	1 1 0	r/m					[
Register-Byte Register-Word Memory-Byte Memory-Word									29 38 35 44	
IDIY = Integer divide (signed):	1 1 1 1 0 1	1 w mod	1 1 1	r/m					14-52 	
Register-Byte Register-Word Memory-Byte Memory-Word AAM = ASCII adjust for multiply	1 1 0 1 0 1		0 0 1 (0 1 0				į.	53-61 50-58 59-67 19	,
AAD = ASCII adjust for divid	le 1 1 0 1 0 1	0 1 0 0	001	0 1 0					15	
CBW = Convert byte to word	100110							ļ	2	
CWD = Convert word to double word	100110	0 1				•		į	4	
LOGIC Shift/rotate instructions: Register/memory by 1 Register/memory by CL	1 1 0 1 0 0		III r					H	2/15 5+n/17 +n	
Register/memory by count	1 1 0 0 0 0	0 w mod	TTT r	/m	coun	t				!
TTT Instruction 0 0 0 ROL 0 0 1 ROR 0 1 0 RCL 0 1 1 RCR 1 0 0 SHL/SAL 1 0 1 SHR 1 1 1 SAR										
		.								
STANDARDIZE		SIZE A								
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T.	ABLE III. <u>Ins</u>	truction	set sum	mary	- Contin	ued.			
Function	Format							Clock cycles	Comments
AND = And: Reg/memory and register to either	0 0 1 0 0 0	d w mod	l reg	r/m				3/10	
Immediate to register/memory	100000	0 w mod	1 0 0	r/m	data	data if w	= 1	4/16	
Immediate to accumulator	0 0 1 0 0 1	0 w	data		data if	w = 1		3/4	8/16-bit
TEST = And function to flags, no result:					1		! 		
Register/memory and register	100001	·	i reg	r/m			 	3/10	
Immediate data and register/ memory	1 1 1 1 0 1	1 w mod	1000	r/m	data	data if w	= 1	4/10	
Immediate data and accumulato	r 1 0 1 0 1 0	0 w	data		data if	w = 1		3/4	8/16-bit
OR = Or: Reg/memory and register to either	0 0 0 0 1 0	d w mod	i reg	r/m]			3/10	
Immediate to register/memory	100000	0 w mod	001	r/m	data	data if w	= 1	4/16	
Immediate to accumulator	0 0 0 0 1 1	0 w	data		data if	w = 1	İ	3/4	8/16-bit
XOR = Exclusive or: Reg/memory and register to either	0 0 1 1 0 0	d w mod	i reg	r/m]			3/10	
Immediate to register/memory	100000	O w mod	1110	r/m	data	data if w	= 1	4/16	
Immediate to accumulator	0 0 1 1 0 1	ρw	data		data if	w = 1		3/4	8/16-bit
NOT = Invert register/memory	1 1 1 1 0 1	1 w mod	010	r/m]			3	
STRING MANIPULATION: MOVS = Move byte/word	1 0 1 0 0 1	0 w						14	
CMPS = Compare byte/word	1 0 1 0 0 1	1 w						22	<u> </u>
SCAS = Scan byte/word	1 0 1 0 1 1	1 w						15	
LODS = Load byte/wd to AL/AX	1 0 1 0 1 1	0 w						12	
STOS = Store byte/wd from AL//	A 1 0 1 0 1 0	1 w						10	
INS = input byte/wd from DX port	0 1 1 0 1 1	0 W						14	
OUTS = Output byte/wd to DX port	0 1 1 0 1 1	1 w						 14 	
			·						
STANDARDIZED	_	SIZE A				850	10		
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TABLE	III. <u>Inst</u>	ruction se	et summary - Co	ntinued.		
Function	Format				 Clock cycles	Comments
STRING MANIPULATION (Continued) Repeated by count in CX	:					
MOVS = Move string	1111	0 0 1 0 1	010010w		8+8n	
CMPS = Compare string	1111	0 0 1 z 1	010011w]	5+22n	
SCAS = Scan string	1111	0 0 1 z 1	010111w]	5+15n	
LODS = Load string	1111	0010	0 1 0 1 1 0 w		6+11n	
STOS = Store string	1 1 1 1	0010	0 1 0 1 0 1 w		6+9n	
INS = Input string	1 1 1 1	0010) 1 1 0 1 1 0 w		8+8n	
OUTS = Output string	1111	0010) 1 1 0 1 1 1 w		8+8n	}
CONTROL TRANSFER						
CALL = Call: Direct within segment	1110	1000	disp-low	disp-high	14	
Register/memory indirect within segment	1 1 1 1	1 1 1 1	mod 0 1 0 r/m		13/19	
Direct intersegment	1 0 0 1	1010	segment off	set	23]
			segment sel	ector		! !
Indirect intersegment	1 1 1 1	1 1 1 1	mod 0 1 1 r/m		38	
JMP = Unconditional jump: Short/long	1 1 1 0	1011	disp-low	•	13	! !
Direct within segment	1 1 1 0	1001	disp-low	disp-high	13	! !
Register/memory indirect within segment	1111	1 1 1 1	mod 1 0 0 r/m]	11/17	
Direct intersegment	1 1 1 0	1010	segment of	fset	13	
			segment sel	ector		j i
Indirect intersegment	1 1 1 1	1 1 1 1	mod 1 0 1 r/m]	26	
RET = Return from CALL: Within segment	1 1 0 0	0 0 1 1			16	
Within seg adding immed to SP	1100	0 0 1 0	data-low	data-high	18	! !
Intersegment	1100	1 0 1 1			22	
Intersegment adding immediate to SP	1100	1 0 1 0	data-low	data-high	25	
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TABLE	III. <u>In</u>	struction	set su	ımmary – Conti	nued.		
Function	Format					 Clock cycles	 Comments
CONTROL TRANSFER (Continued):	0.1.1.1	0.1.0.0		\neg			
JE/JZ = Jump on equal/zero	0 1 1 1		disp	믁		4/13	JMP not taken/JMP
JL/JNGE = Jump on less/not greater or equal	0 1 1 1	1100	disp	<u> </u>		4/13	taken
JLE/JNG = Jump on less or equal/ not greater	0 1 1 1	1 1 1 0	disp			4/13	
JB/JNAE = Jump on below/not above or equal	0 1 1 1	0 0 1 0	disp			4/13	
JBE/JNA = Jump on below or equal/not above	0 1 1 1	0 1 1 0	disp			4/13	
JP/JPE = Jump on parity/parity even	0 1 1 1	1 0 1 0	disp			4/13	
JO = Jump on overflow	0 1 1 1	0000	disp			4/13	
JS = Jump on sign	0 1 1 1	1000	disp	5		4/13	! !
JNE/JNZ = Jump on not equal/ not zero	0 1 1 1	0 1 0 1	disp			4/13	
JNL/JGE = Jump on not less/ greater or equal	0 1 1 1	1 1 0 1	disp			4/13	
JNLE/JG = Jump on not less or equal/greater	0 1 1 1	1 1 1 1	disp			4/13	
JNB/JAE = Jump on not below/ above or equal	0 1 1 1	0 0 1 1	disp			4/13	
JNBE/JA = Jump on not below or equal/above	0 1 1 1	0 1 1 1	disp			4/13	
JNP/JPO = Jump on not par/par odd	0 1 1 1	1011	disp			4/13	
JNO = Jump on not overflow	0 1 1 1	0001	disp			4/13	
JNS = Jump on not sign	0 1 1 1	1001	disp			4/13	
JCXZ = Jump on CX zero	1110	0011	disp			5/15	
LOOP = Loop CX times	1 1 1 0	0010	disp			6/16	
LOOPZ/LOOPE = Loop while zero/ equal	1 1 1 0 (0 0 0 1	disp			6/16	LOOP not taken/LOO taken
LOOPNZ/LOOPNE = Loop while not zero/equal	1 1 1 0 0	0000	disp			6/16	
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TAB	LE III. <u>Ins</u>	truction	set sum	nary - C	ontin	ued.			
Function	Format							 Clock cycles	Comments
ENTER = Enter procedure L = 0 L = 1 L > 1	1 1 0 0 1	000	data-1	ow da	ta-hi	gh	L	 15 25 22+16 (n-1)	
LEAVE = Leave procedure	1 1 0 0 1	001						1 8	
INT = Interrupt: Type specified .	1 1 0 0 1	1 0 1	type					47	
Туре 3	1 1 0 0 1	100							if INT. taken/
INTO = Interrupt on overflow	1 1 0 0 1	110						48/4	lif INT. Inot taken
IRET = Interrupt return	1 1 0 0 1	1 1 1 1						 28 	
BOUND = Detect value out of range	0 1 1 0 0	0 0 1 0	mod reg	r/m]			 33-35 	 - -
PROCESSOR CONTROL CLC = Clear carry	1111	1000						 2	
CMC = Complement carry	1 1 1 1 (0 1 0 1						2	
STC = Set carry	11111	1001						2	1
CLD = Clear direction	1 1 1 1 1	1 1 0 0						2	
STD = Set direction	1 1 1 1 1	1 1 0 1						2	
CLI = Clear interrupt	1 1 1 1 1	1 0 1 0						2	
STI = Set interrupt	1 1 1 1 1	1011						2	!
HLT = Halt	11110	0 1 0 0						2	!
WAIT = Wait	10011	0 1 1						6	 if test = 0
LOCK = Bus lock prefix	1 1 1 1 (0000						2	
ESC = Processor extension esca		ITTT Lare opco		LLL r/n] ension)		6	1
								•	·
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NOTES:

The effective address (EA) of the memory operand is computed according to the mod and r/m fields:

if mod = 11 then r/m is treated as a REG field

if mod = 00 then DISP = 0*, disp-low and disp-high are absent

if mod = 01 then DISP = disp-low sign-extended to 16-bits, disp-high is absent

if mod = 10 then DISP = disp-high: disp-low

if r/m = 000 then EA = (BX) + (SI) + DISP

if r/m = 001 then EA = (BX) + (DI) + DISP

if r/m = 010 then EA = (BP) + (SI) + DISP

if r/m = 011 then EA = (BP) + (DI) + DISP

if r/m = 100 then EA = (SI) + DISP

if r/m = 101 then EA = (DI) + DISP

if r/m = 110 then EA = (BP) + DISP*

if r/m = 111 then EA = (BX) + DISP

DISP follows 2nd byte of instruction (before data if required)

*Except if mod = 00 and r/m = 110 then EA = disp-high: disp-low.

EA calculation time is 4 clock cycles for all modes, and is included in the execution times given whenever appropriate.

SEGMENT OVERRIDE PREFIX

001 reg 110

reg is assigned according to the following:

	Segment
reg	Register
00	ES
01	CS
10	SS
11	DS

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NOTES - Continued.

REG is assigned according to the following table:

16-Bit(w = 1)	8-Bit(w = 0)
000 AX	000 AL
001 CX	001 CL
010 DX	010 DL
011 BX	011 BL
100 SP	100 AH
101 BP	101 CH
110 SI	110 DH
111 DI	111 BH

The physical addresses of all operands addressed by the BP register are computed using the SS segment register. The physical addresses of the destination operands of the string primitive operations (those addressed by the DI register) are computed using the ES segment, which may not be overridden.

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5. PACKAGING

- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.
 - 6. NOTES
- 6.1 Intended use. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
- 6.2 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.4 <u>Symbols</u>, definitions, and functional descriptions. The symbols, definitions, and functional descriptions for this device shall be as follows:

Symbol

Name and function

V_{CC}

System power: +5 volt power supply.

VSS

System ground.

RESET

Reset output indicates that the 80186 CPU is being reset, and can be used as a system reset. It is active HIGH, synchronized with the processor clock, and lasts an integer number of clock periods corresponding to the length of the $\overline{\text{RES}}$ signal.

X1, X2

Crystal inputs, X1 and X2, provide an external connection for a fundamental mode parallel resonant crystal for the internal crystal oscillator. X1 can interface to an external clock instead of a crystal. In this case, minimize the capacitance on X2 or drive X2 with complemented X1. The input or oscillator frequency is internally divided by two to generate the clock signal (CLKOUT).

CLKOUT

Clock output provides the system with a 50 percent duty cycle waveform. All device pin timings are specified relative to CLKOUT.

RES

System reset causes the 80186 to immediately terminate its present activity, clear the internal logic, and enter a dormant state. This signal may be asynchronous to the 80186 clock. The 80186 begins fetching instructions approximately 7 clock cycles after RES is returned HIGH. RES is required to be LOW for greater than 4 clock cycles and is internally synchronized. For proper initialization, the LOW-to-HIGH transition of RES must occur no sooner than 50 microseconds after power up. This input is provided with a Schmitt-trigger to facilitate power-on RES generation via an RC network. When RES occurs, the 80186 will drive the status lines to an inactive level for one clock, and then three-state them.

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TEST TEST is examined by the WAIT instruction. If the TEST input is HIGH when "WAIT" execution begins, instruction execution will suspend. TEST will be

resampled until it goes LOW, at which time execution will resume. If interrupts are enabled while the 80186 is waiting for TEST, interrupts will

be serviced. The input is synchronized internally.

TMR IN O, TMR IN 1

Timer inputs are used either as clock or control signals, depending upon the programmed timer mode. These inputs are active HIGH (or LOW-to-HIGH transitions are counted) and internally synchronized.

TMR OUT O, TMR OUT 1

Timer outputs are used to provide single pulse or continuous waveform generation, depending upon the timer mode selected.

DRQO DRQ1

DMA request is driven HIGH by an external device when it desires that a DMA channel (channel 0 or 1) perform a transfer. These signals are active HIGH. level-triggered, and internally synchronized.

IMN

Non-maskable interrupt is an edge-triggered input which causes a type 2 interrupt. NMI is not maskable internally. A transition from a LOW to HIGH initiates the interrupt at the next instruction boundary. NMI is latched internally. An NMI duration of one clock or more will guarantee service. This input is internally synchronized.

INTO, INT1, INT2/INTAO INT3/INTAI

Maskable interrupt requests can be requested by strobing one of these pins. When configured as inputs, these pins are active HIGH. Interrupt requests are synchronized internally. INT2 and INT3 may be configured via software to provide active-LOW interrupt-acknowledge output signals. All interrupt inputs may be configured via software to be either edge-or level-triggered. To ensure recognition, all interrupt requests must remain active until the interrupt is acknowleged. When iRMX mode is selected, the function of these pins changes.

A19/S6, A18/S5, A17/S4, A16/S3

Address bus outputs (16-19) and bus cycle status (3-6) reflect the four most significant address bits during T1. These signals are active HIGH. During T_2 , T_3 , T_W , and T_4 , status information is available on these lines as encoded below:

	Low	High
\$6	Processor cycle	DMA cycle

S3, S4, and S5 are defined as LOW during T_2-T_4 .

AD15-AD0

Address/data bus (0-15) signals constitute the time multiplexed memory or I/O address (T_1) and data (T_2 , T_3 , T_W , and T_4) bus. The bus is active HIGH A_0 is analogous to BHE for the lower byte of the data bus, pins D_7 through D_0 . It is LOW during T_1 when a byte is to be transferred onto the lower portion of the bus in memory of I/O operations.

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BHE/S7

During T_1 the bus high enable signal should be used to determine if data is to be enabled onto the most significant half of the data bus, pins $D_{15}-D_8$. BHE is LOW during T_1 for read, write, and interrupt acknowledge cycles when a byte is to be transferred on the higher half of the bus. The S7 status information is available during T_2 , T_3 , and T_4 . S7 is logically equivalent to BHE. The signal is active LOW, and is three-stated OFF during bus HOLD.

BHE and AO encodings					
BHE value	AO value	Function			
0	0	Word transfer			
0	1	Byte transfer on upper half of data bus (D ₁₅ -D ₈)			
1	0	Byte transfer on lower half of data bus (D7-D ₀)			
1	1	Reserved			

ALE/QSO

Address latch enable/queue status 0 is provided by the 80186 to latch the address into the address latches. ALE is active HIGH. Addresses are guaranteed to be valid on the trailing edge of ALE. The ALE rising edge is generated off the rising edge of the CLKOUT immediately preceding T_1 of the associated bus cycle. The trailing edge is generated off the CLKOUT rising edge in T_1 . Note that ALE is never floated.

WR/QS1

Write strobe/queue status 1 indicates that the data on the bus is to be written into a memory or an I/O device. WR is active for T_2 , T_3 , and T_W of any write cycle. It is active LOW, and floats during "HOLD." It is driven HIGH for one clock during reset, and then floated. When the 80186 is in queue status mode, the ALE/QSO and WR/QS1 pins provide information about processor instruction queue interaction.

QS1	QS0	Queue operation
0		No queue operation
0	0	First opcode byte fetched from the queue
1	1	Subsequent byte fetched from the queue
1	1	Empty the queue

RD/OSMD

Read strobe indicates that the 80186 is performing a memory or I/O read cycle. $\overline{\text{RD}}$ is active LOW for T_2 , T_3 , and T_W of any read cycle. It is guaranteed not to go LOW in T_2 until after the address bus is floated. $\overline{\text{RD}}$ is active LOW, and floats during "HOLD." $\overline{\text{RD}}$ is driven HIGH for one clock during reset, and then the output driver is floated. A weak internal pull-up mechanism on the $\overline{\text{RD}}$ line holds it HIGH when the line is not driven. During RESET the pin is sampled to determine whether the 80186 should provide ALE, $\overline{\text{WR}}$, and $\overline{\text{RD}}$, or if the queue-status should be provided. $\overline{\text{RD}}$ should be connected to GND to provide queue-status data.

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ARDY

Asynchronous ready informs the 80186 that the addressed memory space or I/O device will complete a data transfer. The ARDY input pin will accept an asynchronous input, and is active HIGH. Only the rising edge is internally synchronized by the 80186. This means that the falling edge of ARDY must be synchronized to the 80186 clock. If connected to $V_{\rm CC}$, no WAIT states are inserted. Asynchronous ready (ARDY) or synchronous ready (SRDY) must be active to terminate a bus cycle.

SRDY

Synchronous ready must be synchronized externally to the 80186. The use of SRDY provides a relaxed system-timing specification on the ready input. This is accomplished by eliminating the one-half clock cycle which is required for internally resolving the signal level when using the ARDY input. This line is active HIGH. If this line is connected to V_{CC} , no WAIT states are inserted. Asynchronous ready (ARDY) or synchronous ready (SRDY) must be active before a bus cycle is terminated. If unused, this line should be tied LOW.

LOCK

LOCK output indicates that other system bus masters are not to gain control of the system bus while $\overline{\text{LOCK}}$ is active LOW. The $\overline{\text{LOCK}}$ signal is requested by the LOCK prefix instruction and is activated at the beginning of the first data cycle associated with the instruction following the LOCK prefix. It remains active until the completion of the instruction following the LOCK prefix. No prefetches will occur while $\overline{\text{LOCK}}$ is asserted. $\overline{\text{LOCK}}$ is active LOW, is driven HIGH for one clock during RESET, and then floated. If unused, this line should be tied LOW.

 $\overline{50}$, $\overline{51}$, $\overline{52}$ Bus cycle status $\overline{50}$ - $\overline{52}$ are encoded to provide bus-transaction information.

	801	86 bus cycl	e status information
<u>52</u>	21.	<u>20</u>	Bus cycle initiated
0	0	0	Interrupt acknowledge
0	0	1	Read I/O
0	1 1	0	Write I/O
0	1 1	1	Halt
1	0	0	Instruction fetch
1	0 1	1	Read data from memory
1	1 1	0	Write data to memory
1	1 1	1	Passive (no bus cycle)
<u> </u>			1

The status pins float during "HOLD."

52 may be used as a logical M/IO indicator, and SI as a DT/R indicator.

The status lines are driven HIGH for one clock during reset, and then floated until a bus cycle begins.

HOLD (input)
HLDA (output)

HOLD indicates that another bus master is requesting the local bus. The HOLD input is active HIGH. HOLD may be asynchronous with respect to the 80186 clock. The 80186 will issue a HLDA (HIGH) in response to a HOLD request at the end of T4 or T1. Simultaneous with the issuance of HLDA the 80186 will float the local bus and control lines. After HOLD is detected as being LOW, the 80186 will lower HLDA. When the 80186 needs to run another bus cycle, it will again drive the local bus and control lines.

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Upper memory chip select is an active LOW output whenever a memory reference is made to the defined upper portion (1K-256K block) of memory. This line is not floated during bus HOLD. The address range activating $\overline{\text{UCS}}$ is software UCS programmable. **LCS** Lower memory chip select is active LOW whenever a memory reference is made to the defined lower portion (1K-256K) of memory. This line is not floated during bus HOLD. The address range activating LCS is software programmable. Mid-range memory chip select signals are active LOW when a memory reference is MCSU-3 made to the defined mid-range portion of memory (8K-512K). These lines are not floated during bus HOLD. The address ranges activating MCSO-3 are software programmable. **PCSO** Peripheral chip select signals 0-4 are active LOW when a reference is made to the defined peripheral area (64K byte I/O space). These lines are not floated during bus HOLD. The address ranges activating $\overline{\text{PCSO}}$ -4 are software programmable. PCST-4 PCS5/A1 Peripheral chip select 5 or latched A_1 may be programmed to provide a sixth peripheral chip select, or to provide an internally latched A1 signal. The address range activating $\overline{PCS5}$ is software programmable. When programmed to provide latched A₁, rather than $\overline{PCS5}$, this pin will retain the previously latched value of $\bar{\mathsf{A}}_1$ during a bus HOLD. A1 is active HIGH. Peripheral chip select 6 or latched A_2 may be programmed to provide a seventh peripheral chip select, or to provide an internally latched A_2 signal. The address range activating PCS6 is software programmable. When programmed to provide latched A_2 , rather than PCS6, this pin will retain the previously PCS6/A2 latched value of \$\tilde{A}_2\$ during a bus HOLD. A2 is active HIGH. Data transmit/receive controls the direction of data flow through the external DT/R data bus transceiver. When LOW, data is transferred to the 80186. When HIGH the 80186 places write data on the data bus. Data enable is provided as a data bus transceiver output enable. DEN is active DEN LOW during each memory and I/O access. DEN is HIGH whenever DT/R changes state.

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- 6.5 Record of users. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6022.
- 6.6 Comments. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone (513) 296-5375.
- 6.7 Approved sources of supply. Approved sources of supply are listed in MIL-BUL-103. Additional sources will be added to MIL-BUL-103 as they become available. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.7) has been submitted to and accepted by DESC-ECS. The approved sources of supply listed below are for information purposes only and are current only to the date of the last action of this document.

Military drawing part number	Vendor CAGE number	Vendor similar part number 1/
8501001ZX	34649 34335	MG80186-8/B 80186/BZC
8501001YX	34649	MQ80186-8/B
8501002ZX	34649 34335	MG80186-6/B 80186-6/BZC
8501002YX	34649	MQ80186-6/B

1/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address
34335	Advanced Micro Devices 901 Thompson Place P.O. Box 3453 Sunnyvale, CA 94081
34649	Intel Corporation 3065 Bowers Avenue Santa Clara, CA 95051

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